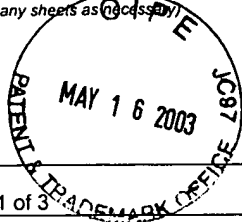


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Application Number	10/028001
Filing Date	December 20, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Tu-Tu Ho

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Attorney Docket No: 1303.035US1

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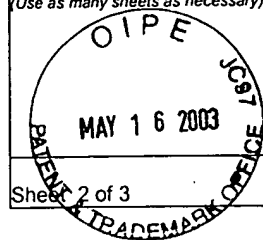
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Group Art Unit	2818
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